

20V P-Channel MOSFETs

General Description

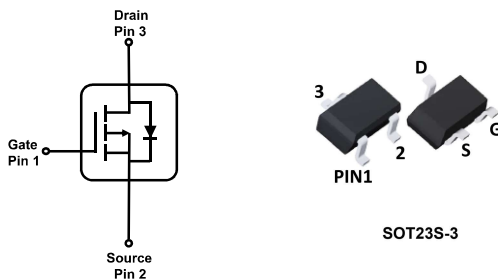
These P-Channel enhancement mode power field effect transistors are using trench - technology. This advanced technology is designed to minimize on-state resistance, provide superior switching performance. This devices are well suited for high efficiency fast switching applications.

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-20V	44m Ω	-4.8A

Features

- Fast Switching
- Low Gate Drive
- Low Gate Charge

Pin Configuration



Applications

- PWM
- Load Switch

Absolute Maximum Ratings ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-Source Voltage		-20	V
V_{GS}	Gate-Source Voltage		± 10	
I_D	Drain Current-Continuous ^A	$T_A = 25^\circ\text{C}$	-4.8	A
		$T_A = 70^\circ\text{C}$	-3.2	
I_{DM}	Drain Current-Pulsed ^{A, B}	$T_A = 25^\circ\text{C}$	-16	A
I_{AS}	Non-repetitive Avalanche Current ^E		-14	A
E_{AS}	Single Pulse Drain-to-Source Avalanche Energy ^E		9.8	mJ
P_D	Maximum Power Dissipation	$T_A = 25^\circ\text{C}$	1.6	W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
$R_{\theta JA}$	Junction-to-Ambient ^C	Steady State	80	$^\circ\text{C/W}$